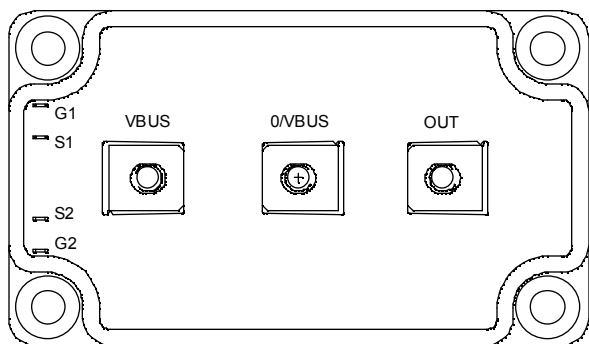
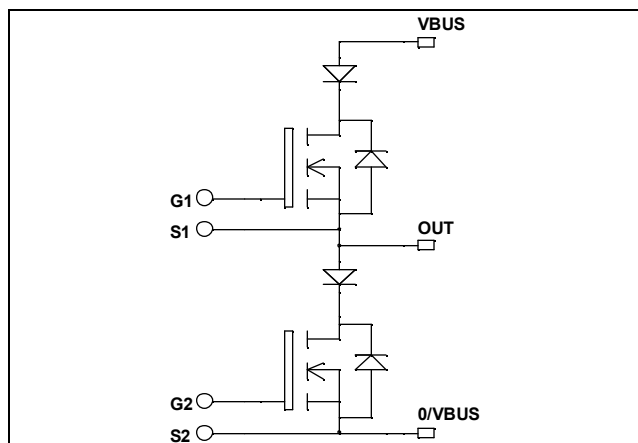


Phase leg with Series diodes MOSFET Power Module

$$V_{DSS} = 1000V$$

$$R_{DSon} = 130m\Omega \text{ typ @ } T_j = 25^{\circ}C$$

$$I_D = 65A \text{ @ } T_c = 25^{\circ}C$$



Application

- Zero Current Switching resonant mode

Features

- Power MOS 7[®] MOSFETs
 - Low R_{DSon}
 - Low input and Miller capacitance
 - Low gate charge
 - Fast intrinsic reverse diode
 - Avalanche energy rated
 - Very rugged
- Kelvin source for easy drive
- Very low stray inductance
 - Symmetrical design
 - M5 power connectors
- High level of integration

Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Low profile
- RoHS Compliant

Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
V_{DSS}	Drain - Source Breakdown Voltage	1000	V
I_D	Continuous Drain Current	$T_c = 25^{\circ}C$	A
		$T_c = 80^{\circ}C$	
I_{DM}	Pulsed Drain current	240	
V_{GS}	Gate - Source Voltage	± 30	V
R_{DSon}	Drain - Source ON Resistance	156	m Ω
P_D	Maximum Power Dissipation	$T_c = 25^{\circ}C$	W
I_{AR}	Avalanche current (repetitive and non repetitive)	24	A
E_{AR}	Repetitive Avalanche Energy	30	mJ
E_{AS}	Single Pulse Avalanche Energy	1300	



CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

All ratings @ $T_j = 25^\circ\text{C}$ unless otherwise specified

Electrical Characteristics

<i>Symbol</i>	<i>Characteristic</i>	<i>Test Conditions</i>	<i>Min</i>	<i>Typ</i>	<i>Max</i>	<i>Unit</i>
I_{DSS}	Zero Gate Voltage Drain Current	$V_{GS} = 0V, V_{DS} = 1000V$			600	μA
		$V_{GS} = 0V, V_{DS} = 800V$			2	mA
$R_{DS(on)}$	Drain – Source on Resistance	$V_{GS} = 10V, I_D = 32.5A$		130	156	$m\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 6mA$	3		5	V
I_{GSS}	Gate – Source Leakage Current	$V_{GS} = \pm 30V, V_{DS} = 0V$			± 450	nA

Dynamic Characteristics

<i>Symbol</i>	<i>Characteristic</i>	<i>Test Conditions</i>	<i>Min</i>	<i>Typ</i>	<i>Max</i>	<i>Unit</i>
C_{iss}	Input Capacitance	$V_{GS} = 0V$		15.2		nF
C_{oss}	Output Capacitance	$V_{DS} = 25V$		2.6		
C_{rss}	Reverse Transfer Capacitance	$f = 1MHz$		0.42		
Q_g	Total gate Charge	$V_{GS} = 10V$		562		nC
Q_{gs}	Gate – Source Charge	$V_{Bus} = 500V$		75		
Q_{gd}	Gate – Drain Charge	$I_D = 65A$		363		
$T_{d(on)}$	Turn-on Delay Time	Inductive switching @ 125°C $V_{GS} = 15V$ $V_{Bus} = 667V$ $I_D = 65A$ $R_G = 0.5\Omega$		9		ns
T_r	Rise Time			9		
$T_{d(off)}$	Turn-off Delay Time			50		
T_f	Fall Time			24		
E_{on}	Turn-on Switching Energy	Inductive switching @ 25°C $V_{GS} = 15V, V_{Bus} = 667V$ $I_D = 65A, R_G = 0.5\Omega$		2.13		mJ
E_{off}	Turn-off Switching Energy			0.46		
E_{on}	Turn-on Switching Energy	Inductive switching @ 125°C $V_{GS} = 15V, V_{Bus} = 667V$ $I_D = 65A, R_G = 0.5\Omega$		4.4		mJ
E_{off}	Turn-off Switching Energy			0.57		

Series diode ratings and characteristics

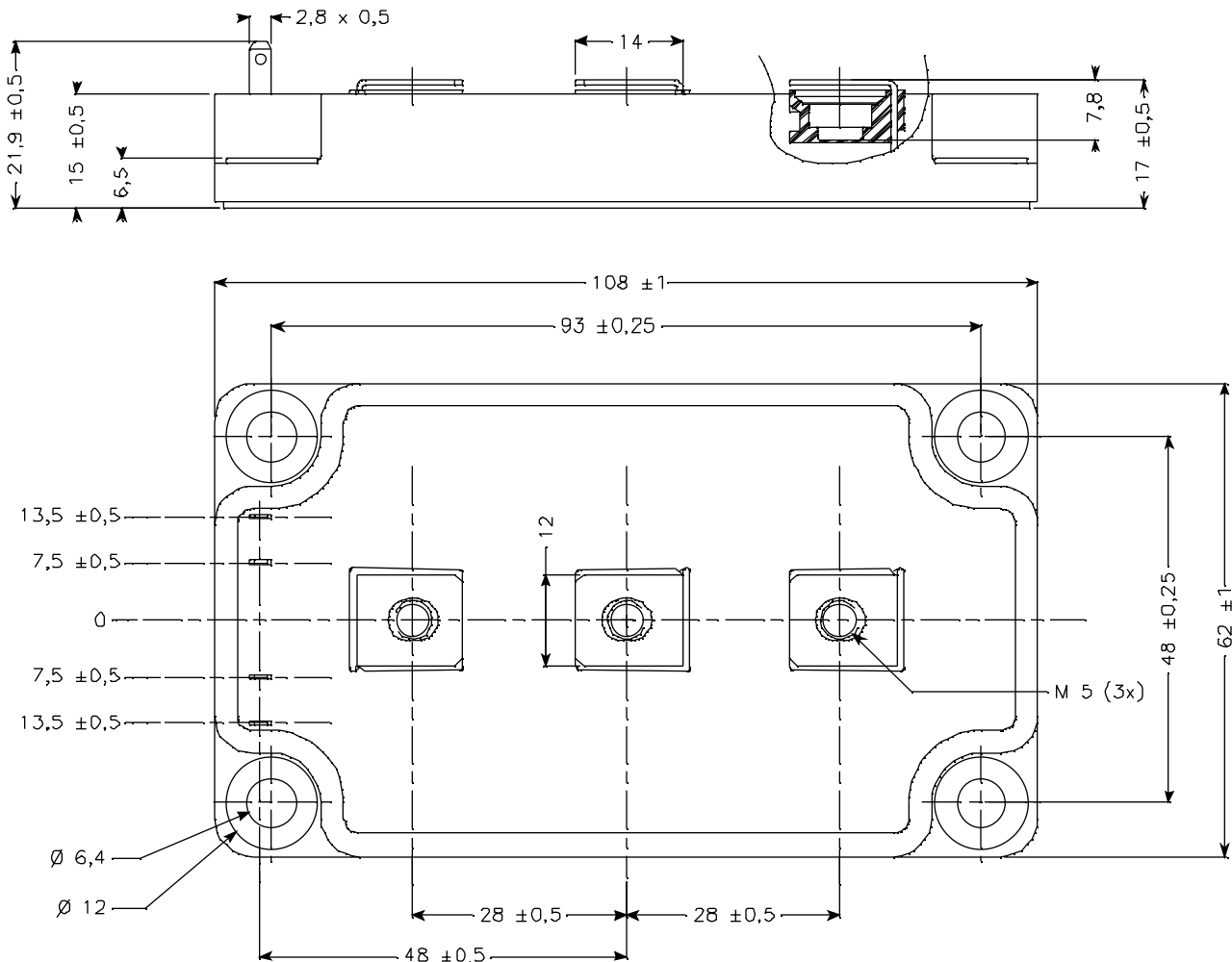
<i>Symbol</i>	<i>Characteristic</i>	<i>Test Conditions</i>	<i>Min</i>	<i>Typ</i>	<i>Max</i>	<i>Unit</i>
V_{RRM}	Maximum Repetitive Reverse Voltage		1200			V
I_{RM}	Maximum Reverse Leakage Current	$V_R = 1200V$	$T_j = 25^\circ\text{C}$		150	μA
			$T_j = 125^\circ\text{C}$		600	
I_F	DC Forward Current	$T_c = 100^\circ\text{C}$		120		A
V_F	Diode Forward Voltage	$I_F = 120A$		2.5	3	V
		$I_F = 240A$		3		
		$I_F = 120A$	$T_j = 125^\circ\text{C}$	1.8		
t_{rr}	Reverse Recovery Time	$I_F = 120A$ $V_R = 800V$ $di/dt = 400A/\mu s$	$T_j = 25^\circ\text{C}$	265		ns
			$T_j = 125^\circ\text{C}$	350		
Q_{rr}	Reverse Recovery Charge		$T_j = 25^\circ\text{C}$	1120		nC
			$T_j = 125^\circ\text{C}$	5800		

Thermal and package characteristics

Symbol Characteristic

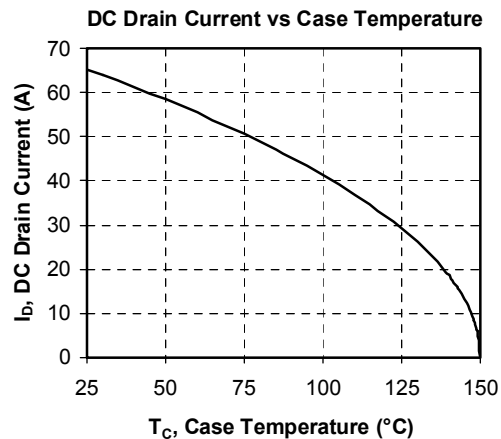
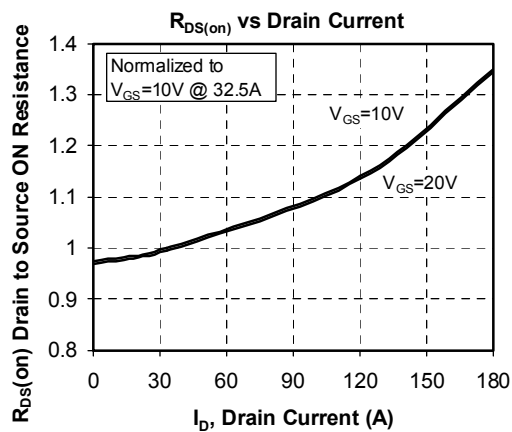
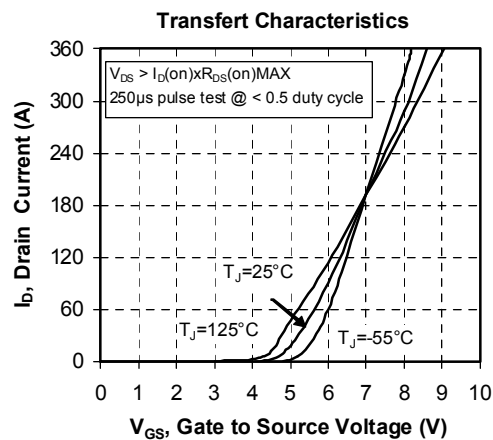
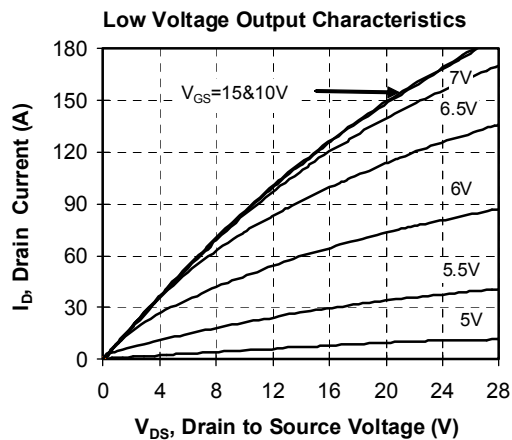
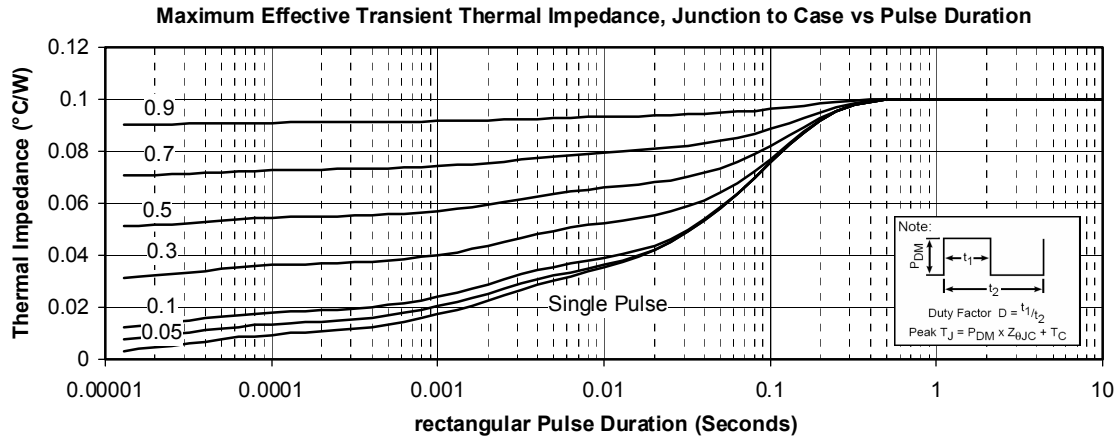
			Min	Typ	Max	Unit
R_{thJC}	Junction to Case Thermal Resistance	Transistor			0.10	°C/W
		Series diode			0.46	
V_{ISOL}	RMS Isolation Voltage, any terminal to case $t=1$ min, $I_{isol}<1mA$, 50/60Hz		2500			V
T_J	Operating junction temperature range		-40		150	°C
T_{STG}	Storage Temperature Range		-40		125	
T_C	Operating Case Temperature		-40		100	
Torque	Mounting torque	To heatsink M6	3		5	N.m
		For terminals M5	2		3.5	
Wt	Package Weight				280	g

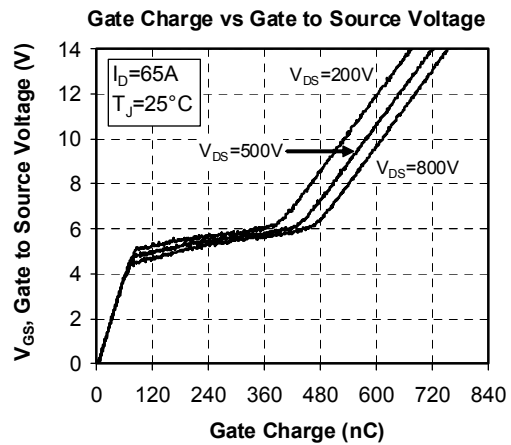
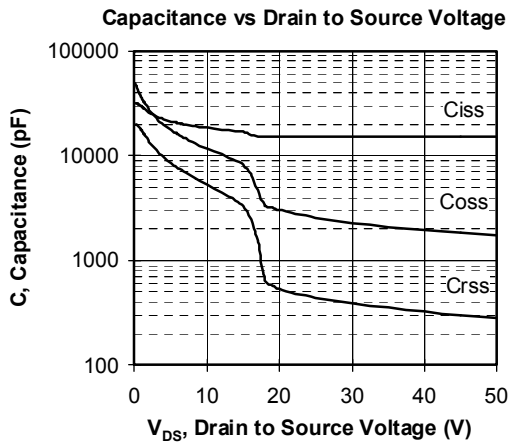
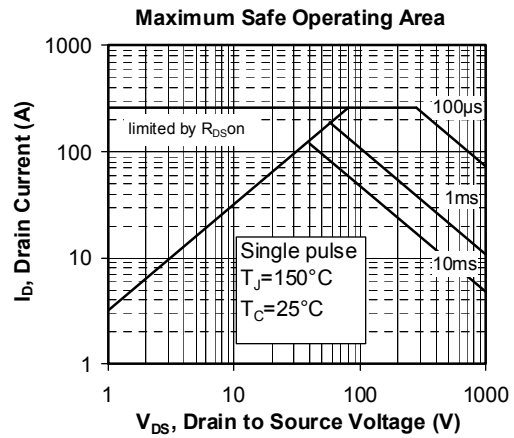
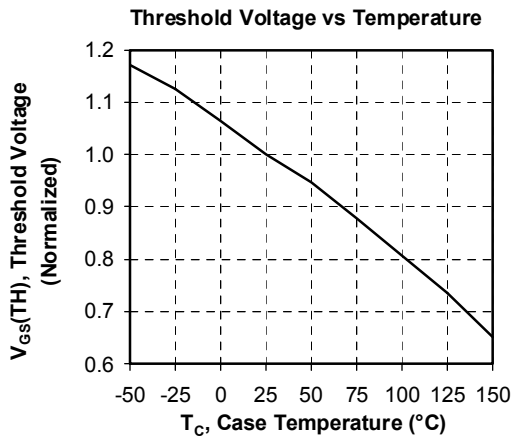
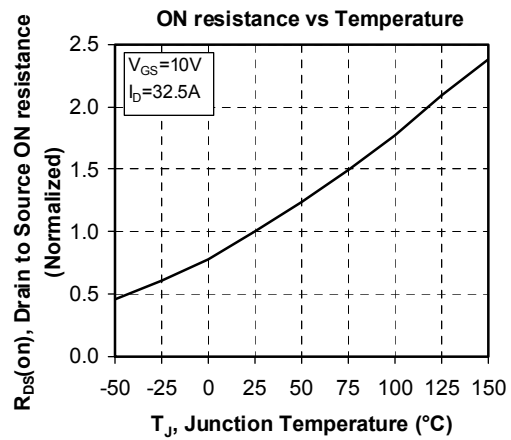
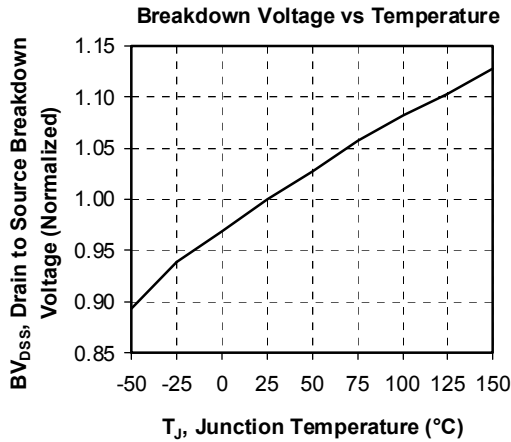
SP6 Package outline (dimensions in mm)

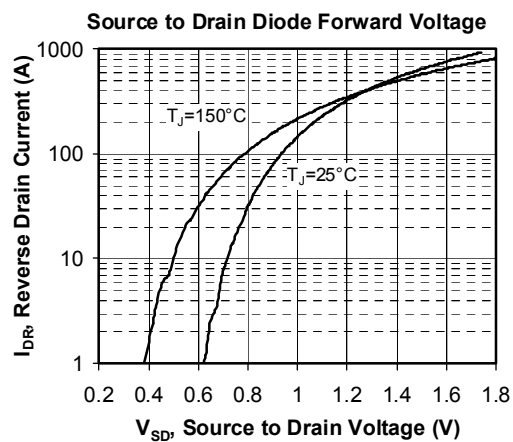
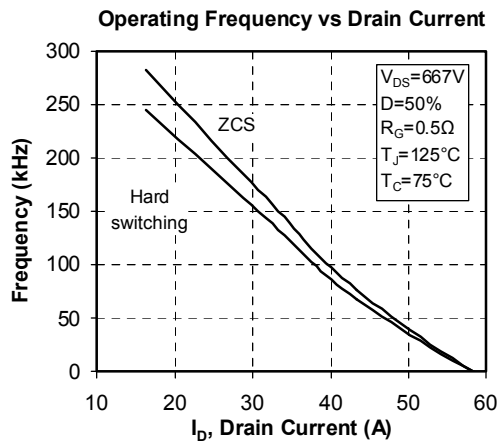
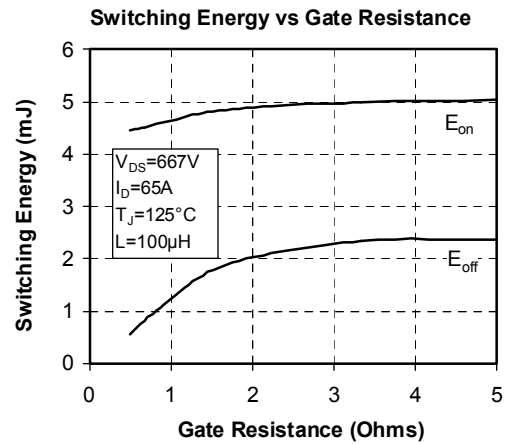
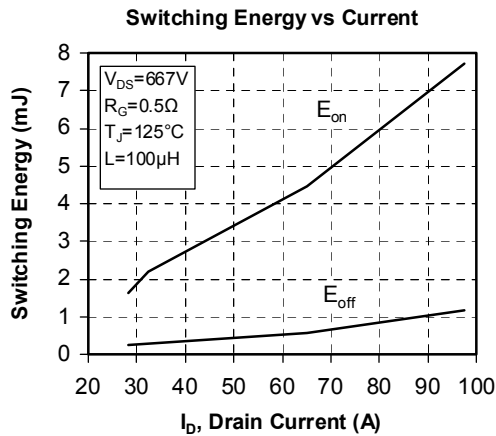
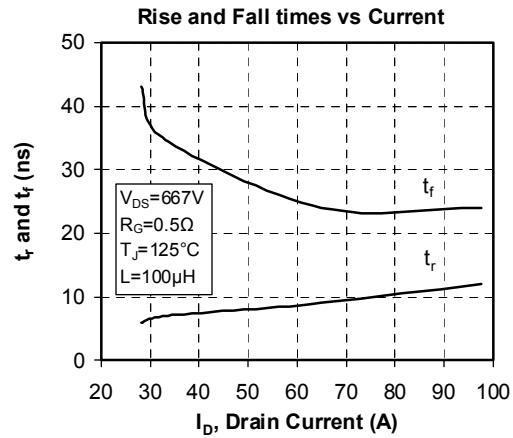
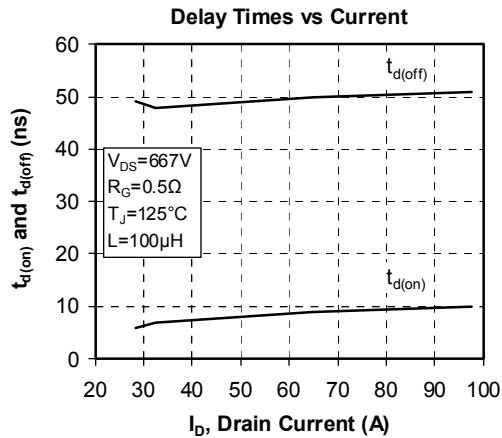


See application note APT0601 - Mounting Instructions for SP6 Power Modules on www.microsemi.com

Typical Performance Curve







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